Giant Ferroelectric Resistance Switching Controlled by Lowâ€Power Neuromorphic Inâ€Memory Computing

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Citation Report

#	Article	IF	Citations
1	A Marr's Threeâ€Level Analytical Framework for Neuromorphic Electronic Systems. Advanced Intelligent Systems, 2021, 3, 2100054.	3.3	3
2	Neuromorphic computing: Devices, hardware, and system application facilitated by two-dimensional materials. Applied Physics Reviews, 2021, 8, .	5.5	39
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